

1N34
Gold Bonded Germanium Diode

FEATURES

Low forward voltage drop—low power consumption
Thirty years of proven reliability—one million hours mean time between failures (MTBF)
Very low noise level
Metallurgically bonded

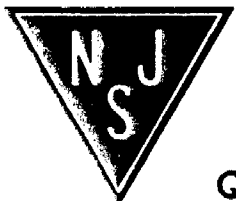
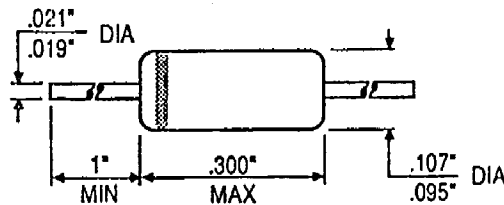
ABSOLUTE MAXIMUM RATINGS (at 25 °C, unless otherwise specified)

Peak Inverse Voltage 60 Volts
Peak Forward Current 500 mA
Operating Temperature Range - 65 °C to 85 °C
Average Power Dissipation 80 mW

ELECTRICAL CHARACTERISTICS

	Symbol	Conditions	Min	Max	Unit	T °C
Peak Inverse Voltage	PIV	1 mA	60		V	25 °C
Reverse Current	I _r	10 V		15	μA	25 °C
Reverse Current	I _r	50 V		800	μA	°C
Forward Voltage	V _f	8.5 mA		1	V	25 °C

MECHANICAL



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